



# 2332 STATIC READ ONLY MEMORY (4096x8)

#### DESCRIPTION

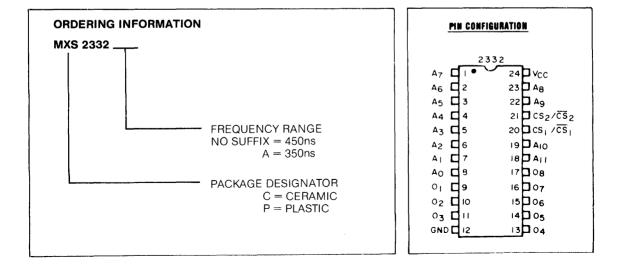
The 2332 high performance read only memory is organized 4096 words by 8 bits with access times of less than 350 ns. This ROM is designed to be compatible with all microprocessor and similar applications where high performance, large bit storage and simple interfacing are important design considerations. This device offers TTL input and output levels.

The 2332 operates totally asynchronously. No clock input is required. The two programmable chip select inputs allow four 32K ROMS to be OR-tied without external decoding.

Designed to replace two 2716 16K EPROMS, the 2332 can eliminate the need to redesign printed circuit boards for volume mask programmed ROMS after prototyping with EPROMS.

- 4096 x 8 Bit Organization
- Single +5 Volt Supply
- Access Time 2332 450 ns 2332A 350 ns
- Completely TTL Compatible
- Totally Static Operation

- Three-State Outputs for Wire-OR Expansion
- Two Programmable Chip Selects
- Pin Compatible with 2716 & 2732 EPROM
- Replacement for Two 2716s
- 2708/2716 EPROMS Accepted as Program Data Inputs
- 400mV Noise Immunity on Inputs



### ABSOLUTE MAXIMUM RATINGS

Ambient Operating Temperature	0° to +70°C
Storage Temperature	-65°C to +150°C
Supply Voltage to Ground Potential	-0.5V to +7.0V
Applied Output Voltage	-0.5V to +7.0V
Applied Input Voltage	-0.5V to +7.0V
Power Dissipation	1.0W

#### COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

## D.C. CHARACTERISTICS

 $T_A = 0^{\circ}C$  to +70°C,  $V_{CC} = 5.0V \pm 5\%$  (unless otherwise specified)

Symbol	Parameter	Min.	Max.	Units	Test Conditions
ICC1	Power Supply Current		100	mA	$V_{IN} = V_{CC}, V_O = Open, T_A = 0^{\circ}C$
ICC2	Power Supply Current		95	mA	$V_{IN} = V_{CC}, V_O = Open, T_A = 25^{\circ}C$
<sup>1</sup> 0	Output Leakage Current		10	μA	Chip Deselected, $V_{O} = 0$ to $V_{CC}$
lj –	Input Load Current		10	μΑ	$V_{CC} = Max. V_{IN} = O to V_{CC}$
VOL	Output Low Voltage		0.4	Volts	$V_{CC} = Min. I_{OL} = 2.1 mA$
VOH	Output High Voltage	2.4		Volts	$V_{CC} = Min. I_{OH} = -400 \mu A$
VIL	Input Low Voltage	-0.5	0.8	Volts	See note 1
v <sub>IH</sub>	Input High Voltage	2.0	V <sub>CC</sub> +1	Volts	

## A. C. CHARACTERISTICS

 $T_A = 0^{\circ}C$  to  $+70^{\circ}C$ ,  $V_{CC} = 5.0V \pm 5\%$  (unless otherwise specified)

Symbol	Parameter	2332		2332A		Units	Test Conditions
		Min.	Max.	Min.	Max.		
<sup>t</sup> ACC	Address Access Time		450		350	ns	
tco	Chip Select Delay		200		200	ns	
<sup>t</sup> DF	Chip Deselect Delay		175		175	ns	See Note 2
tон	Previous Data Valid After Address Change Delay	40		40		ns	

## CAPACITANCE

 $T_A = 25^{\circ}C$ , f = 1.0MHz, See Note 3

Symbol	Parameter	Min.	Max.	Units	Test Conditions
C <sub>IN</sub>	Input Capacitance		8	pF	All Pins except Pin under
C <sub>OUT</sub>	Output Capacitance		10	pF	Test Tied to AC Ground

Note 1: Input levels that swing more negative than -0.5V will be clamped and may cause damage to the device.

2-142

Note 2: Loading 1 TTL + 100 pF, input transition time: 20 ns.

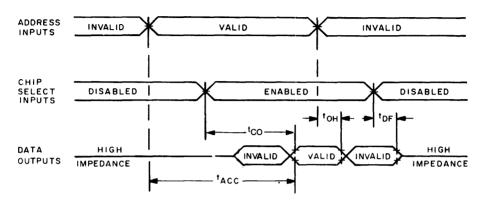
Timing measurement levels: input 1.5V, output 0.8V and 2.0V.  $C_L = 100 \, pF$ .

Note 3: This parameter is periodically sampled and is not 100% tested.

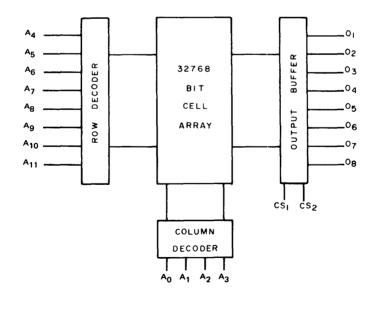




TIMING DIAGRAM



BLOCK DIAGRAM







TYPICAL CHARACTERISTICS

